MT4606

Dual N & P-Channel PowerTrench® MOSFET

MT Semiconductor®

http://www.mtsemi.com

General Description

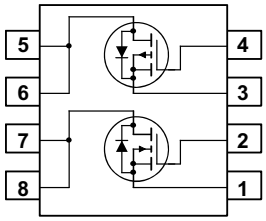
These dual N and P-Channel enhancement mode power field effect transistors are produced using MOS-TECH Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Features

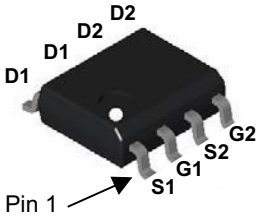
- N-Channel
  30V/5A
  $R_{DS(on)}$ = 0.018Ω @ V_{GS} = 10V
  $R_{DS(on)}$ = 0.027Ω @ V_{GS} = 4.5V
- P-Channel
  -30V/-5A
  $R_{DS(on)}$ = 0.026Ω @ V_{GS} = -10V
  $R_{DS(on)}$ = 0.044Ω @ V_{GS} = -4.5V

Simplified Schematic



MARKING DIAGRAM & PIN ASSIGNMENT

SO-8



Absolute Maximum Ratings (T$_A$ = 25℃ unless otherwise noted)

Symbol	Parameter		N-CH	P-CH	Units
V_{DSS}	Drain-Source Voltage		30	-30	V
V_{GSS}	Gate-Source Voltage		±20	±20	V
I_D	Drain Current - Continuous	(Note 1a)	5	-5	A
	- Pulsed		20	-20	
P_D	Power Dissipation for Dual Operation		2		W
	Power Dissipation for Single Operation	(Note 1a)	1.6		
		(Note 1b)	1		
		(Note 1c)	0.9		
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150		°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

Electrical Characteristics T_A = 25°C unless otherwise noted

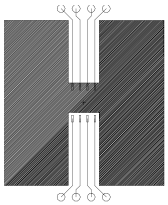
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Off Characteristics							
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA V_{GS} = 0 V, I_D = -250 µA	N-CH P-CH	30 -30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C I_D = -250 µA, Referenced to 25°C	N-CH P-CH		25 -22		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V V_{DS} = -24 V, V_{GS} = 0 V	N-CH P-CH			1 -1	µA
I_{GSSF}	Gate-Body Leakage, Forward	V_{GS} = 20 V, V_{DS} = 0 V	All			100	nA
I_{GSSR}	Gate-Body Leakage, Reverse	V_{GS} = -20 V, V_{DS} = 0 V	All			-100	nA
On Characteristics (Note 2)							
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA V_{DS} = V_{GS}, I_D = -250 µA	N-CH P-CH	1 -1	1.6 -1.7	3 -3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C I_D = -250 µA, Referenced to 25°C	N-CH P-CH		-4.3 4		mV/°C
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 5 A V_{GS} = 10 V, I_D = 5 A, T_J = 125°C V_{GS} = 4.5 V, I_D = 4 A	N-CH		18 32 27	30 42 40	mΩ
		V_{GS} = -10 V, I_D = -5 A V_{GS} = -10 V, I_D = -5 A, T_J = 125°C V_{GS} = -4.5 V, I_D = -4 A	P-CH		26 48 44	54 78 80	
$I_{D(on)}$	On-State Drain Current	V_{GS} = 10 V, V_{DS} = 5 V V_{GS} = -10 V, V_{DS} = -5 V	N-CH P-CH	20 -20			A
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 5 A V_{DS} = -5 V, I_D =-5 A	N-CH P-CH		19 11		S
Dynamic Characteristics							
C_{iss}	Input Capacitance	N-CH V_{DS} = 10 V, V_{GS} = 0 V, f = 1.0 MHz P-CH V_{DS} = -10 V, V_{GS} = 0 V, f = 1.0 MHz	N-CH P-CH		460 493		pF
C_{oss}	Output Capacitance		N-CH P-CH		56 65		pF
C_{rss}	Reverse Transfer Capacitance		N-CH P-CH		50.5 44		pF

Electrical Characteristics (continued) T_A = 25°C unless otherwise noted

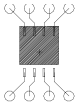
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Switching Characteristics (Note 2)							
$t_{d(on)}$	Turn-On Delay Time	N-CH V_{DD} = 10 V, I_D = 1 A, V_{GS} = 10V, R_{GEN} = 6 Ω P-CH V_{DD} = -10 V, I_D = -1 A, V_{GS} = -10V, R_{GEN} = 6 Ω	N-CH P-CH		4.5 7.2		ns
t_r	Turn-On Rise Time		N-CH P-CH		3.1 4.8		ns
$t_{d(off)}$	Turn-Off Delay Time		N-CH P-CH		22 25		ns
t_f	Turn-Off Fall Time		N-CH P-CH		4.0 8.5		ns
Q_g	Total Gate Charge	N-CH V_{DS} = 15 V, I_D = 7 A, V_{GS} = 10 V P-CH V_{DS} = -15 V, I_D = -5 A, V_{GS} = -10 V	N-CH P-CH		6.4 8.2		nC
Q_{gs}	Gate-Source Charge		N-CH P-CH		1.2 0.8		nC
Q_{gd}	Gate-Drain Charge		N-CH P-CH		0.7 2.7		nC
Drain–Source Diode Characteristics and Maximum Ratings							
I_S	Maximum Continuous Drain-Source Diode Forward Current		N-CH P-CH			1.3 -1.3	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 1.3 A (Note 2) V_{GS} = 0 V, I_S = -1.3 A (Note 2)	N-CH P-CH		0.74 -0.76	1.2 -1.2	V

Notes:

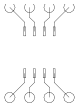
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 78°/W when mounted on a 0.5 in^2 pad of 2 oz copper



b) 125°/W when mounted on a .02 in^2 pad of 2 oz copper



c) 135°/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

Typical Characteristics: N-CH

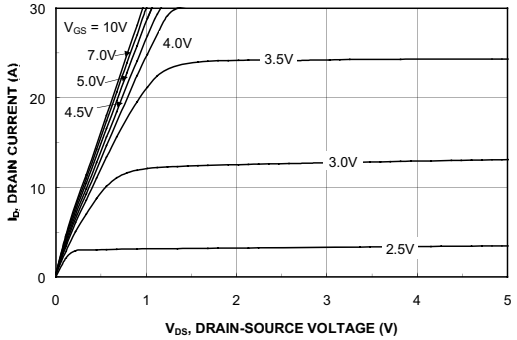


Figure 1. On-Region Characteristics.

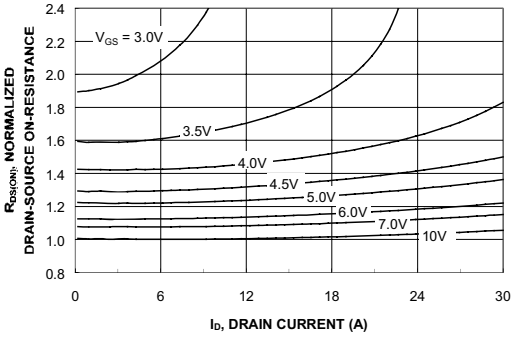


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

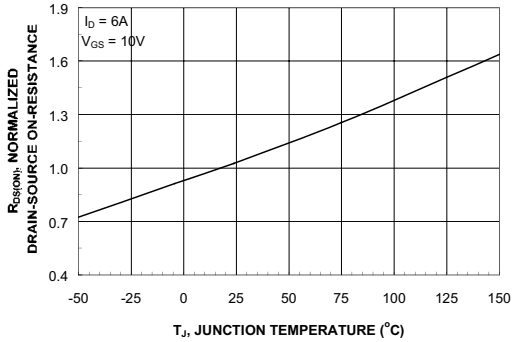


Figure 3. On-Resistance Variation with Temperature.

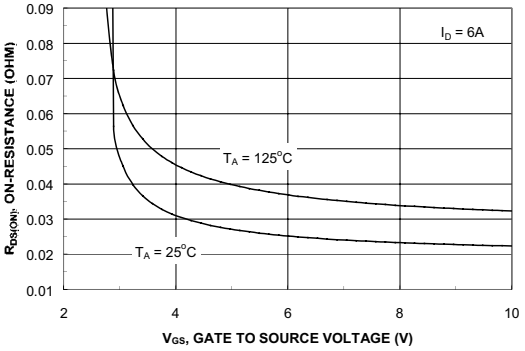


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

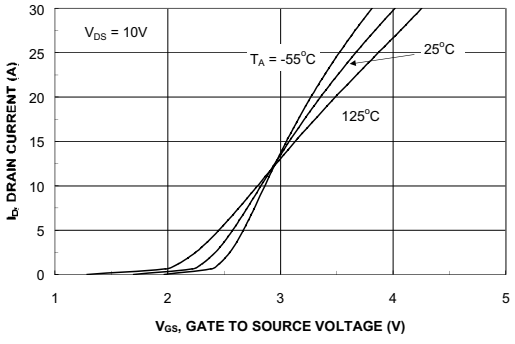


Figure 5. Transfer Characteristics.

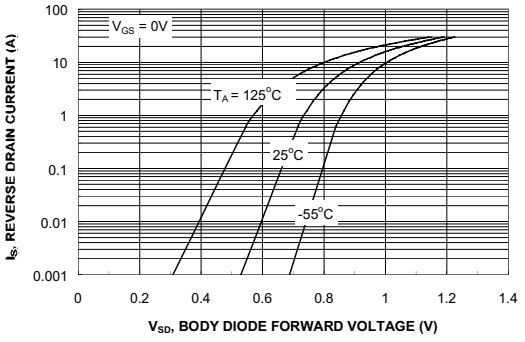


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics: N-CH

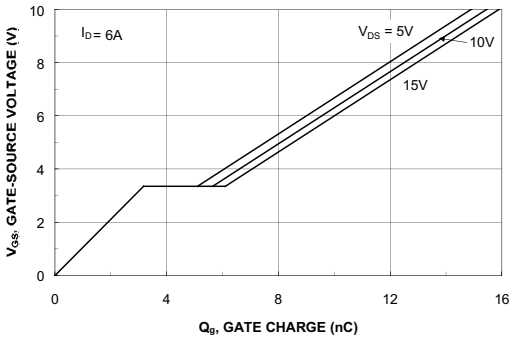


Figure 7. Gate Charge Characteristics.

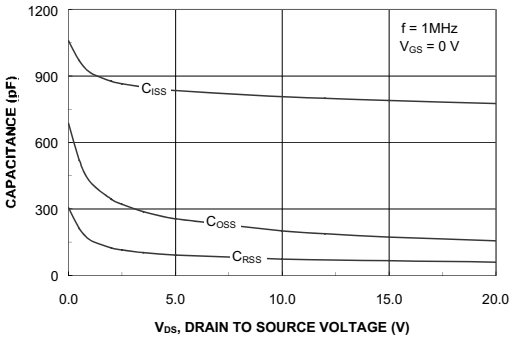


Figure 8. Capacitance Characteristics.

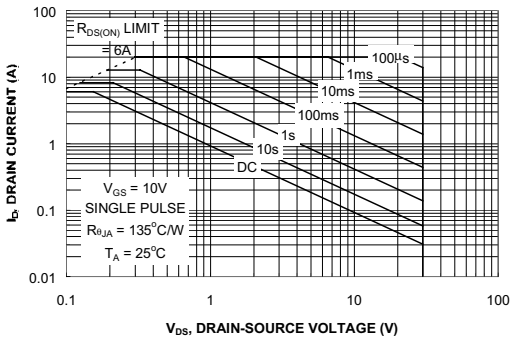


Figure 9. Maximum Safe Operating Area.

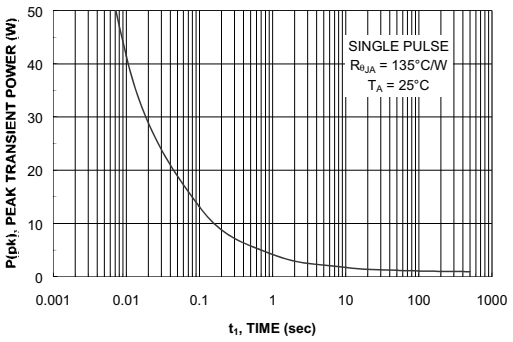


Figure 10. Single Pulse Maximum Power Dissipation.

Typical Characteristics P-CH

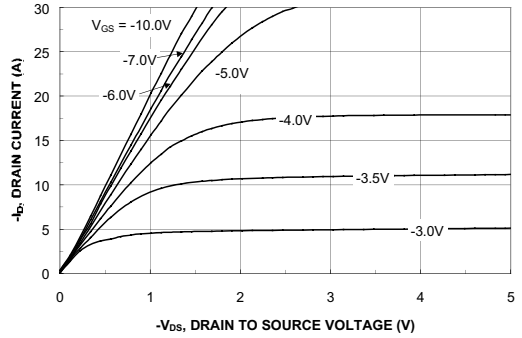


Figure 11. On-Region Characteristics.

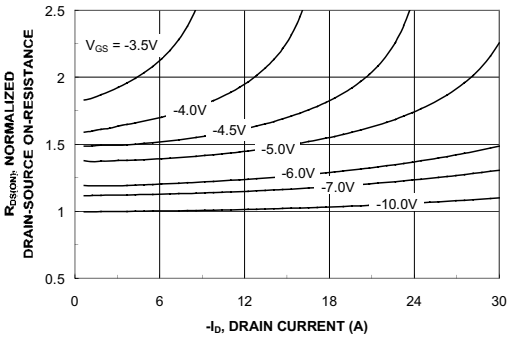


Figure 12. On-Resistance Variation with Drain Current and Gate Voltage.

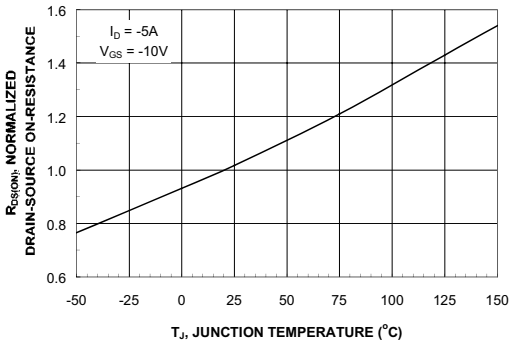


Figure 13. On-Resistance Variation with Temperature.

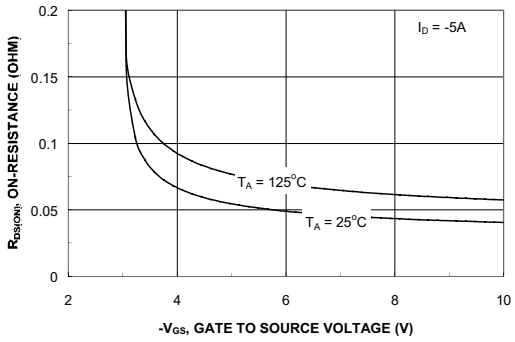


Figure 14. On-Resistance Variation with Gate-to-Source Voltage.

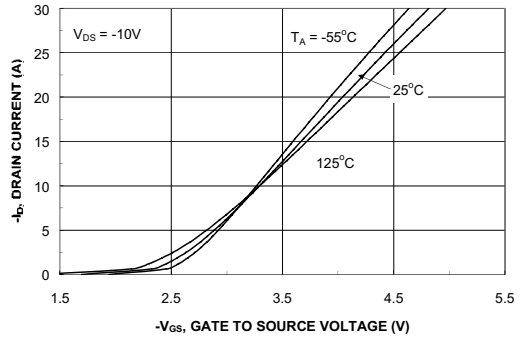


Figure 15. Transfer Characteristics.

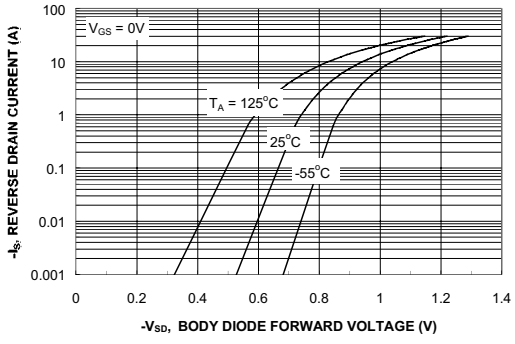


Figure 16. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics P-CH

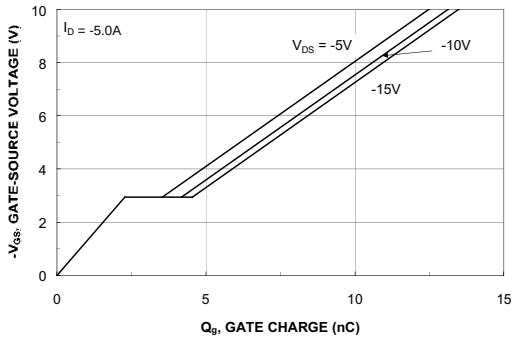


Figure 17. Gate Charge Characteristics.

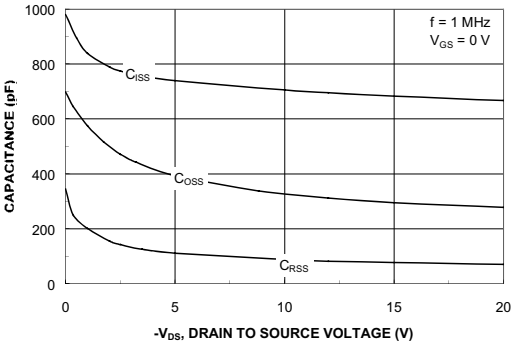


Figure 18. Capacitance Characteristics.

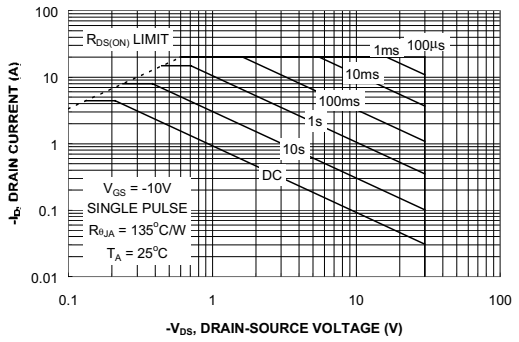


Figure 19. Maximum Safe Operating Area.

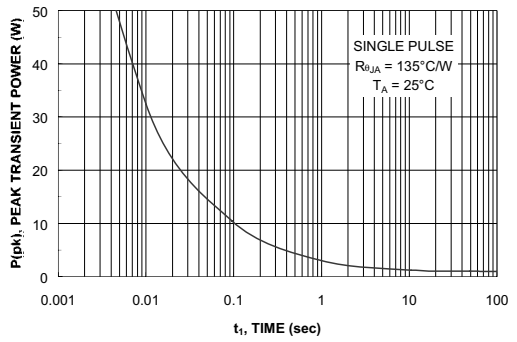


Figure 20. Single Pulse Maximum Power Dissipation.

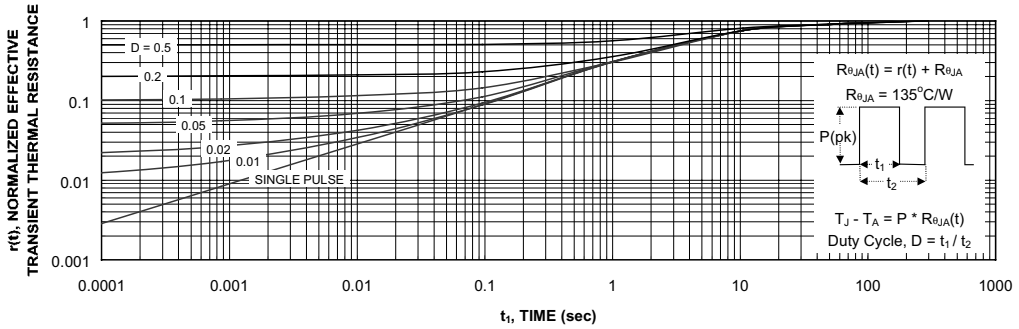


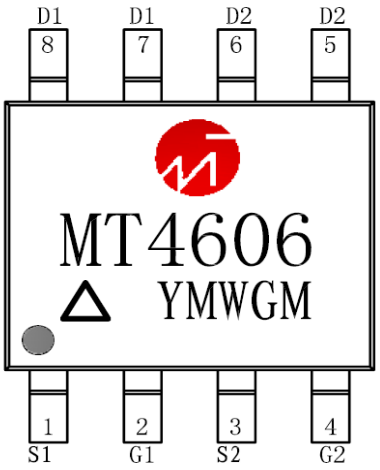
Figure 21. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

Part Marking Information

SO-8 (PMG Code)

SO-8 Devices



MT4606 = Example Base Part Number
● = Pin 1 Indicator
△ = ESD Symbol
Y = Year Code
M = Month Code
W = Week Code
GM = Assembly Factory Code

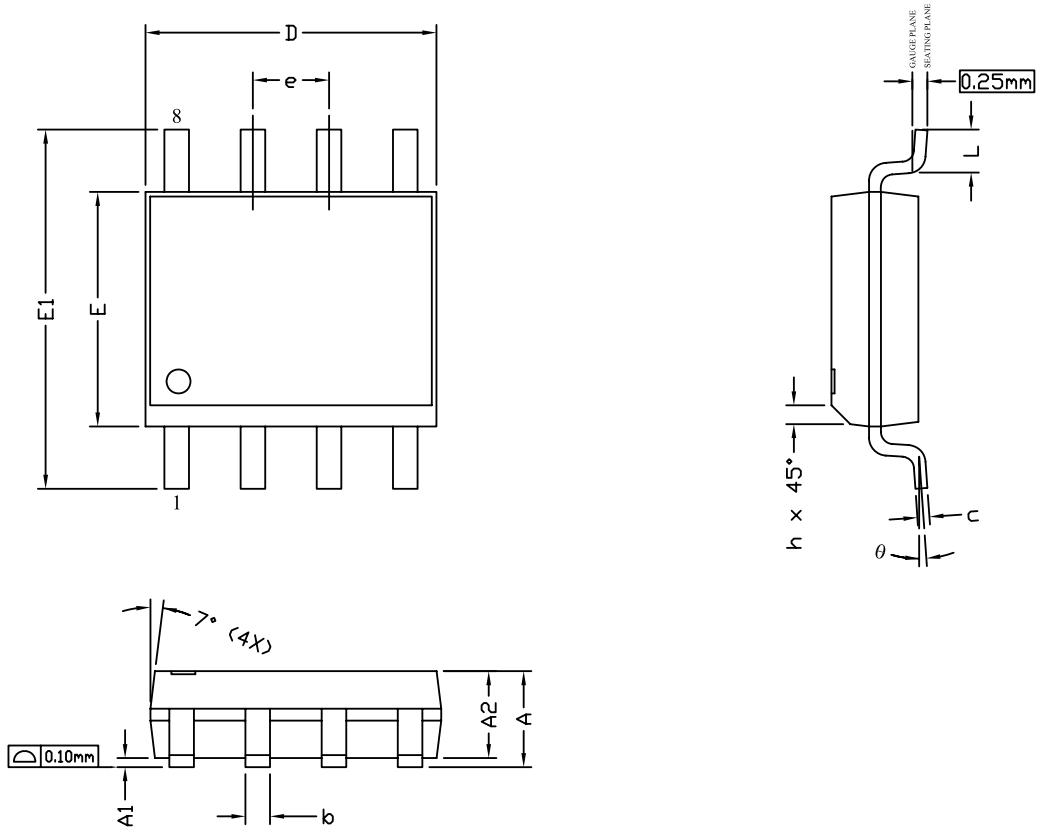
NOTE:

1. For analog switches base part includes DG prefix. Package suffix may or may not be present, depending on room available.

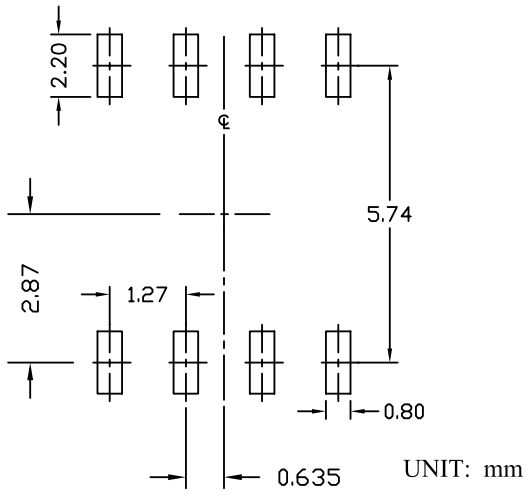
The current marking strategy is reflected. Contact your local sales representative for historical marking strategies for these packages.

Document No.	PO−00004
Version	rev H

SO8 PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



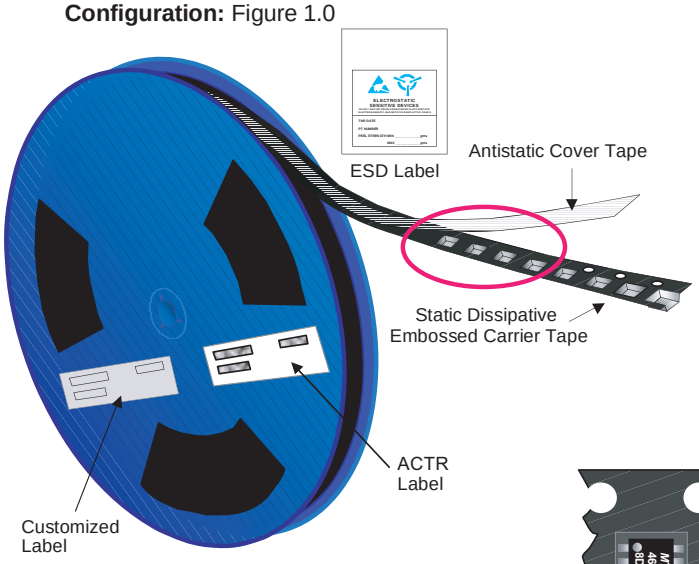
UNIT: mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.35	1.65	1.75	0.053	0.065	0.069
A1	0.10	----	0.25	0.004	----	0.010
A2	1.25	1.50	1.65	0.049	0.059	0.065
b	0.31	----	0.51	0.012	----	0.020
c	0.17	----	0.25	0.007	----	0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
E	3.80	3.90	4.00	0.150	0.154	0.157
e	1.27 BSC			0.050 BSC		
E1	5.80	6.00	6.20	0.228	0.236	0.244
h	0.25	----	0.50	0.010	----	0.020
L	0.40	----	1.27	0.016	----	0.050
θ	0°	----	8°	0°	----	8°

NOTE
1. ALL DIMENSIONS ARE IN MILLMETERS.
2. DIMENSIONS ARE INCLUSIVE OF PLATING.
3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
   MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
4. DIMENSION L IS MEASURED IN GAUGE PLANE.
5. CONTROLLING DIMENSION IS MILLIMETER.
   CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

SOIC-8 Tape and Reel Data

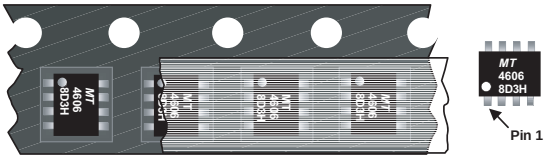
SOIC(8lds) Packaging
Configuration: Figure 1.0



Packaging Description:

SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 330cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 500 units per 7" or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.

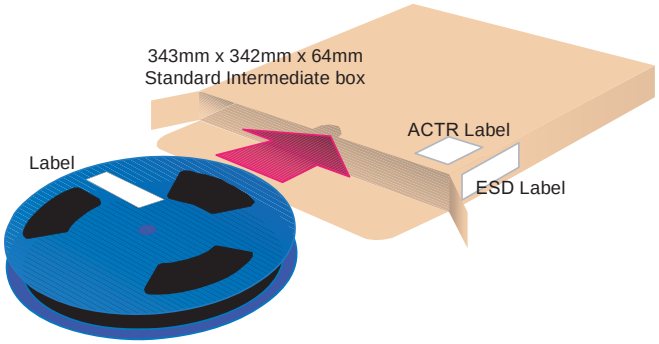


SOIC-8 Unit Orientation

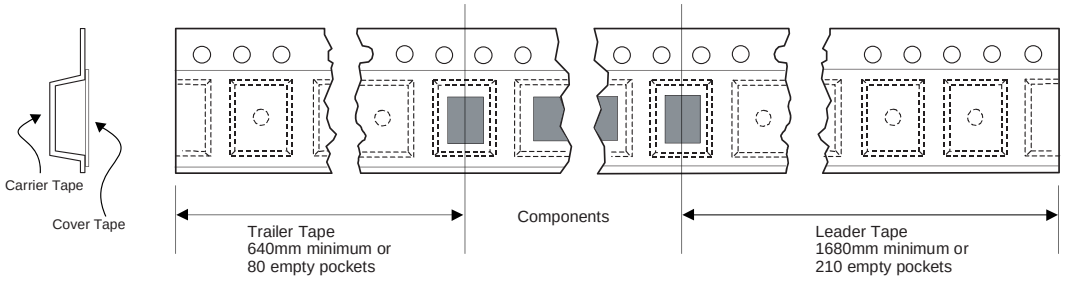
SOIC (8lds) Packaging Information				
Packaging Option	Standard (no flow code)	L86Z	F011	D84Z
Packaging type	ACTR	Rail/Tube	TNR	TNR
Qty per Reel/Tube/Bag	4,000	95	4,000	500
Reel Size	13" Dia	-	13" Dia	7" Dia
Box Dimension (mm)	343x64x343	530x130x83	343x64x343	184x187x47
Max qty per Box	5,000	30,000	8,000	1,000
Weight per unit (gm)	0.0774	0.0774	0.0774	0.0774
Weight per Reel (kg)	0.6060	-	0.9696	0.1182
Note/Comments				

MT4606ACTR Label sample

XH1 MT4606ACTR 4000 QTY: 4000
XH2 C97H22K2-8D3H-K143 P6070561 SPEC:
-MOS-TECH SEMICONDUCTOR LTD-



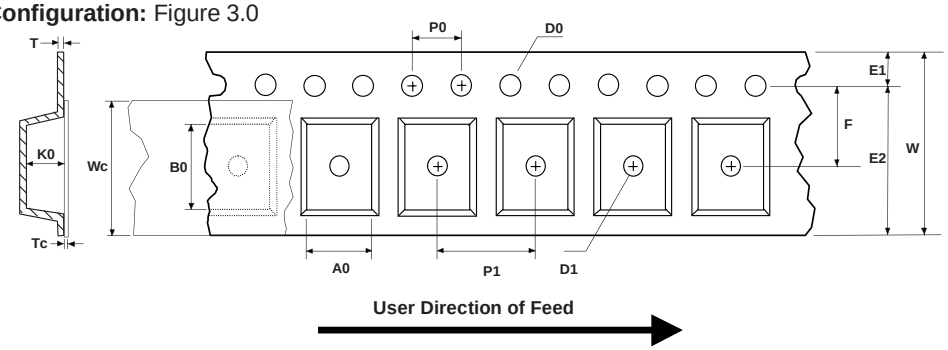
SOIC(8lds) Tape Leader and Trailer
Configuration: Figure 2.0



SOIC-8 Tape and Reel Data, continued

SOIC(8lds) Embossed Carrier Tape

Configuration: Figure 3.0

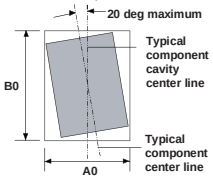


Dimensions are in millimeter														
Pkg type	**A0**	**B0**	**W**	**D0**	**D1**	**E1**	**E2**	**F**	**P1**	**P0**	**K0**	**T**	**Wc**	**Tc**
SOIC(8lds) (12mm)	6.50 +/-0.10	5.30 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

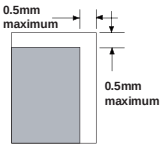
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

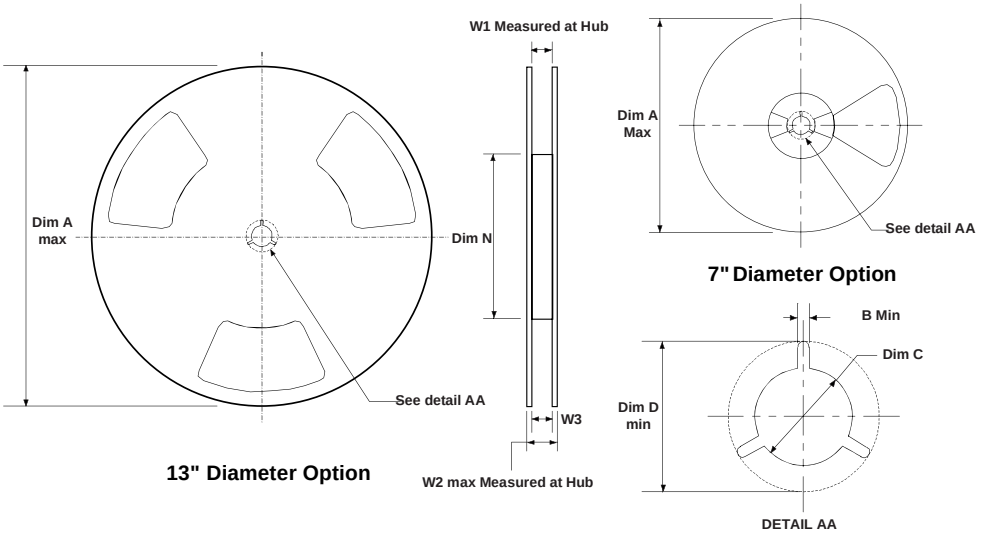


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

SOIC(8lds) Reel Configuration: Figure 4.0



Dimensions are in inches and millimeters									
Tape Size	**Reel Option**	**Dim A**	**Dim B**	**Dim C**	**Dim D**	**Dim N**	**Dim W1**	**Dim W2**	**Dim W3 (LSL-USL)**
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 – 0.606 11.9 – 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 – 0.606 11.9 – 15.4

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